

Fermi Levels

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Fermi Levels

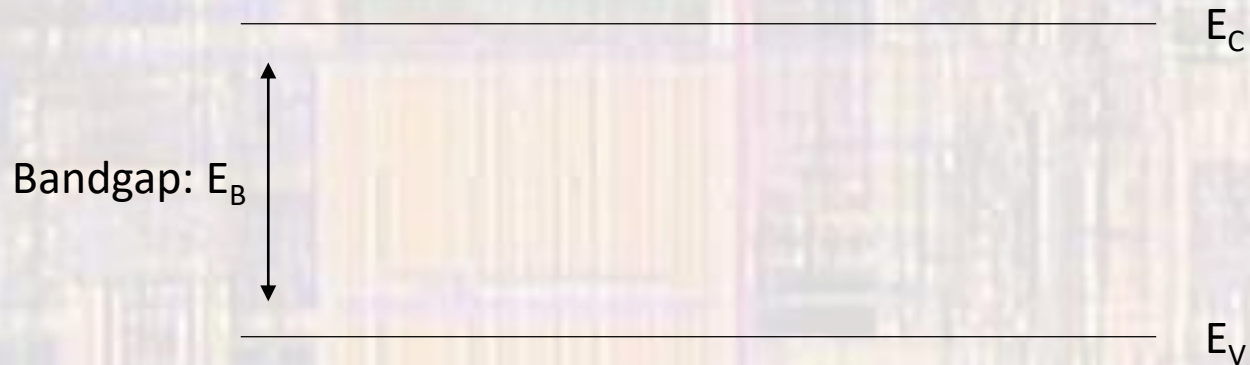
- Electrons and Holes
 - Charge
 - Electron (n) -1.6×10^{-19} Coulomb
 - Hole (p) $+1.6 \times 10^{-19}$ Coulomb
 - Effective mass
 - Mass of a free electron
 - $m_0 = 9.109 \times 10^{-31}$ kilograms
 - Effective mass of an electron in a silicon crystal
 - $m_n^* = 1.1 \times m_0$
 - Effective mass of a hole in a silicon crystal
 - $m_p^* = 0.59 \times m_0$

Fermi Levels

- Electrons and Holes
 - Intrinsic carrier concentration – room temp Si
 - $n_i \cong 10^{10} / \text{cm}^3$
 - Electron/Hole concentrations – room temp Si
 - $n = p = n_i \cong 10^{10} / \text{cm}^3$
 - Charge neutral
 - Note – the density of Si atoms in a crystal is $5 \times 10^{22} / \text{cm}^3$
 - 2 carriers for every 5 trillion atoms

Fermi Levels

- Band Diagrams

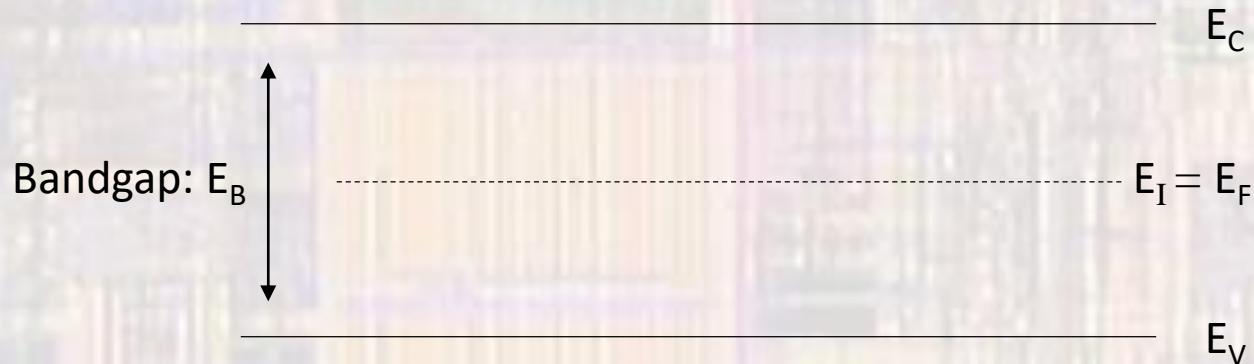


Fermi Levels

- Band Diagrams
 - Fermi Level
 - Indicates the energy level at which half of the possible states are filled with electrons
 - For our purposes the Fermi Level will be used to:
 - Indicate the type of a material
 - Calculate carrier concentrations
 - Analyze semiconductor devices

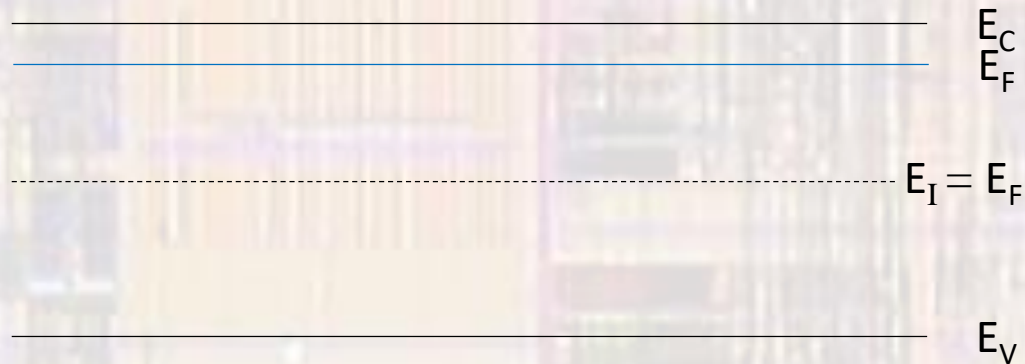
Fermi Levels

- Band Diagrams
 - Fermi Level – Intrinsic
 - $E_I \sim$ mid bandgap



Fermi Levels

- Band Diagrams
 - Fermi Level: n-type doping
 - E_F near E_C
 - Indicates an excess of electrons in the material



Fermi Levels

- Band Diagrams
 - Fermi Level: p-type doping
 - E_F near E_V
 - Indicates an excess of holes in the material

